### **WEDNESDAY AM**

MC Av	vards Ceremony & Plena	ary Sess	ion Music Building, Lotte Lehmann
3:20 am			EMC Awards Ceremony
3:30 am	Darrell Schlom	*PL01	Suboxide Molecular-Beam Epitaxy
9:20 am			BREAK
	o III-Nitrides – Devices		Music Building, Lotte Lehmann
0:00 am	Yu-Hsin Chen	A01	(Student) High Electron Density AlN/GaN/AlGaN Quantum-Well HEMTs on Al-Polar Single-Crystal AlN Substrates
0:20 am	Joseph Dill	A02	(Student) Measurement of Hole Velocity vs. Electric Field in Polarization-Induced Two-Dimensional Hole Gases in GaN/AIN Heterojunctions
0:40 am	Abdullah Mamun	A03	Al <sub>0.84</sub> Ga <sub>0.38</sub> N Channel MOSHFET on Single Crystal Bulk AIN Substrate for Co-Designed Power Electronics
1:00 am	Jiahao Chen	A04	(Student) Record Low Sheet Resistivity (<250 Ω/∎) in High Composition (>35%) and Thick (>30 nm) Crack-Free Strain Optimized Barrier AlGaN/AIN/GaN HEMT on Sapphire
1:20 am	Thai-Son T. Nguyen	A05	(Student) Epitaxial Growth and Transport Properties of AlScN/GaN FerroHEMTs
1:40 am	Dawei Wang	A06	(Late News) Reliability Study and Analysis of Vertical GaN Power Devices
: 2D M	aterials Properties and	Interfac	es UC, Corwin East
0:00 am	Mingfei Xu	B01	(Student) Investigation of Dielectric Properties of h-BN/c-BN Nanocomposites
0:20 am	Shakir Bin Mujib	B02	Reliability of Electronics Containing 2D Materials
0:40 am	Suzanne Mohney	B03	Doping and Damage of MoS, Monolayers from Metal Deposition
1:00 am	Zubaer Hossain	B04	Strain-Induced Magnetism in Defective Graphene
1:20 am	Quazi Deen Mohd Khosru	B05	Graphene-Polymar Mono Defect Based Octonacci Quasi-Photonic Dual Narrowband Absorber
1:40 am	Jennifer Elizabeth DeMell	B06	(Student) Temperature Dependent Spin Transport and Thermally Driven Quantum Phase Change
1. 10 am	Common Enzagoth Bowlon	500	in Graphene/Pb <sub>0.24</sub> Sn <sub>0.76</sub> Te Heterostructure Two-Dimensional Electron Gas
: Photo	onic Devices		UC, Flying A Studios
0:00 am	James Bork	C01	(Student) (In)AlBiAs-Based Short-Wave Infrared Avalanche Photodiodes
):20 am	Subhashree Seth	C02	(Student) Optically Pumped 1200 nm InAs Dot-in-Well (DWELL) Photonic Crystal Surface-Emitting Laser (PCSEL) by Molecular Beam Epitaxy
0:40 am	Jingze Zhao	C03	(Student) Long-Wave Infrared Beam Steering with InAsSb Phased Arrays
1:00 am	Aaron Engel	#C04	(Student) Molecular Beam Epitaxy of Strained Superlattice InAlGaAs/AlGaAs Spin-Polarized Photocathodes
1:20 am	Alexander Timothy Newell	C05	(Student) Sensitivity Optimization in Diffusion-Limited Infrared Detectors
1:40 am	Kevin Kucharczyk	C06	(Student) Development of GaAs Photodetector Arrays for Soft X-Ray Beam Position Monitoring
	scale Characterization	000	
		DO4	UC, State Street
0:00 am 0:20 am	Andrey Krayev Haoxue Yan	D01 D02	TERS Imaging—Unique Nanoscale Technique for Characterization of 2D Materials and Their Lateral/Vertical Heterostructur Rapid Characterization of Threading Dislocations in Diamond via Coincident Cathodoluminescence and Electron
			Channeling Contrast Imaging
0:40 am	Carlo Requiao daCunha	D03	Estimating the Background Potential of Quantum Constrictions Using Scanning Gate Microscopy and Machine Learning
1:00 am	Stephen M. Bankson	D04	(Student) Characterization of Surface Morphology and Superconducting Performance of Thin Aluminum Films Deposited via Thermal Evaporation at Tilted Angles
1:20 am	Robert Stroud	D05	TESCAN TENSOR a 4D-STEM for Multimodal Characterization of Challenging and Interesting Specimens
1:40 am	Michael Evan Liao	D06	Investigation of Extended Defects in Single Crystal Calcite Substrates Using High Resolution X-Ray Topography
: Heter	o-Integration, Intercon	nects an	d Packaging UC, Santa Barbara Harbor
0:00 am	Muhannad Bakir	E01	Heterogeneous Multi-Die Stitching Enabled by Compressible Microinterconnects (CMIs)
0:20 am	Bilal Azhar	E02	(Student) Quasi-2D Materials for Ultra-Low Resistance Electrical Interconnects
0:40 am	Gangtae Jin	E03	Dimensional Scaling of Topological Metal Nanowires for Interconnect
1:00 am	Kenny Huynh	E04	Stability of Interface Morphology and Thermal Boundary Conductance of Direct Wafer Bonded GaN Si Heterojunction Interfaces Annealed at Growth and Annealing Temperatures
1:20 am	Bhargav Yelamanchili	E05	(Student) Superconducting Resonators with Closely Spaced Resonant Frequencies for Material Loss Measurements
1:40 am	Rohan Sengupta	E06	(Student, Late News) Improvement of Heterogeneously Integrated InGaAs/GaN Junctions via Post-Bonding Annealing for Next-Generation Transistors
: Galliu	m Oxide Devices		MCC, MCC Theater
0:00 am	Sushovan Dhara	#F01	(Student) [100] and [010] Oriented β-Ga <sub>2</sub> O <sub>3</sub> Trench Schottky Barrier Diodes with Improved On-Resistance Using
		F02	Low Damage Atomic Ga Etching  (Student) Forward and Reverse Current Transport of (001) β-Ga <sub>2</sub> O <sub>3</sub> Schottky Barrier Diodes and TiO <sub>2</sub> /β-Ga <sub>2</sub> O <sub>3</sub>
0:20 am	Nolan Hendricks		Heterojunction Diodes with Various Schottky Metals
0:40 am	Esmat Farzana	F03	Vertical β-Ga <sub>2</sub> O <sub>3</sub> Diodes with High Barrier PtOx Contacts and High-k TiO <sub>2</sub> Field Plate on Low-Doped Epitaxy for High Breakdown Voltage
1:00 am	Joseph Spencer	F04	(Student) Platinum Oxide Schottky Contacts to Highly-Doped (-201) β-Ga <sub>2</sub> O <sub>3</sub>
	Takumi Ohtsuki	F05	Application of (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> as Back Barrier in Lateral Ga <sub>2</sub> O <sub>3</sub> Radio-Frequency Field-Effect Transistors
1:20 am 1:40 am		F06	(Student) Demonstration of Gallium Oxide Nano-Pillar Field Emitter Arrays

<sup>\*</sup>Plenary Talk # Student Finalist for Oral Presentation

### WEDNESDAY PM

G: Grou	p III-Nitrides — Vertical Po	wer De	vices Music Building, Lotte Lehmanr
1:30 pm	Caleb Glaser	G01	(Student) Improving Electrical Performance of GaN-on-GaN MOS Devices Via Optimized Atomic Layer Deposition of $Al_2O_3$ Gate Dielectrics
:50 pm	Dawei Wang	G02	Design and Fabrication of AlGaN/GaN Multiple P-Channel Schottky Barrier Diodes
:10 pm	Md. Tahmidul Alam	G03	(Student) TCAD-Based Comprehensive Analysis of High Voltage (>600 V) Bidirectional AlGaN/GaN HEMTs
:30 pm	LeighAnn Sarah Larkin	G04	Alpha Radiation Damage Assessment in GaN by Time-Resolved Luminescence Spectroscopy
:50 pm	Mina Moradnia	G05	(Student) Crack-Free III-N Epitaxial Growth on Si (111) Substrate Exceeding 1 µm in Thickness
:10 pm			BREAK
:30 pm	Zhiyu Xu	G06	(Student) 1.2kV Vertical GaN PIN Rectifiers with Nitrogen-Implanted Floating Guard Rings as Edge Termination and Breakdown Characteristics Correlation Study by Wafer-Level Photoluminescence Mapping
50 pm	Henryk Turski	G07	Exploiting Competition Between Built-in Polarization and P-N Junction Field in III-Nitride Heterostructures
10 pm	Mona Ebrish	G08	Contacting p-GaN Efficiently—Why the Same Metal Stacks Give Different Results?
30 pm	Christopher M. Matthews	G09	(Student) Electrical Characterization of AIN PN Diodes
:50 pm	Ziyi He	G10	(Student) Effect of Impact Ionization Coefficients on High-Voltage Vertical AIN Power Devices
l: 2D M	laterials, Devices and Se	nsors	UC, Corwin Eas
30 pm	Juntae Jang	H01	(Student) Reduced Scattering in Remote Surface Charge Transfer Doped MoS <sub>2</sub> Field Effect Transistors
50 pm	Ruixue Li	H02	(Student) Electrical Characterization and Contact Resistance to ALD-Deposited WNbS <sub>2</sub> Thin Films
10 pm	Yun Ping Chiu	H03	(Student) Surface Polarization Engineering Design of 2D Janus MoSSe Complementary Field Effect Transistors
30 pm	Daniel Lewis	H04	(Student) Non-Conductive Electron Transport Through a Quasi-Freestanding Epitaxial Graphene-Insulator Heterostructure Towards a Vacuum-Independent X-Ray Source
:50 pm	Ghanshyam Das Varma	H05	Humidity Tolerant Low Power-Consumption Flexible α-Fe <sub>2</sub> O <sub>3</sub> /rgO/PANI Ternary Nanocomposite for NO <sub>2</sub> Gas Sensing at Room Temperature
:10 pm			BREAK
30 pm	Saad Bhuiya	H06	(Student) Graphene/III-As Nanosheets—Self-Assembly, Electrical Transport and Potential for THz Generation
50 pm	Frances Camille Masim Wu	#H07	(Student) Control of Dark Exciton Dynamics in Suspended WSe, Monolayer via Electrostatic Deflection
10 pm	Claire Ganski	H08	(Student) Effects of Strain and Local Topography on Electromechanical Coupling in Monolayer Transition Metal Dichalcogenides
30 pm	Ying-Chuan Chen	H09	(Student) Studies of 2D Material Resistive Random-Access Memory by Kinetic Monte Carlo Simulation
50 pm	Ramesh G. Mani	H10	Electrically Detected Spin Resonance in Graphene
Novel	IR Detector Materials		UC, Flying A Studios
:30 pm	Charles W. Tu	101	The Effects of Strain Compensation in Type-II InGaAs/GaAsSb Quantum Wells Grown on GaAs(001) Substrates
50 pm	Jingze Zhao	102	(Student) Minority Carrier Lifetime and Mobility in Bulk InAsSb for High Quantum Efficiency LWIR Detectors
10 pm	Rachel Corey White	103	(Student) Optical and Structural Properties of InSb-Based Dilute-Bismide Alloys Grown by Molecular Beam Epitaxy
30 pm	Amberly Ricks	104	(Student) Bismuth Incorporation in AllnSb for Wide-Bandgap Barriers on InSb
50 pm	Fatih Furkan Ince	105	(Student) MBE Growth of InSb Quantum Well on InAs (100) Using AlInSb Buffer Layer
10 pm			BREAK
	Materials Epitaxy		UC, Flying A Studios
30 pm	Pooja Donthi Reddy	J01	(Student) Single-Phase Orthorhombic SnSe-PbSe Alloy Thin Films Stabilized on GaAs by Molecular Beam Epitaxy
50 pm	Morgan Bergthold	J02	(Student) Photoluminescence Efficiency and Minority Carrier Lifetime of Type-II Superlattices on GaAs  Using an Interfacial Misfit Array
10 nm	Leland Joseph Nordin	J03	PbSe Mid-Infrared Light Emitting Diodes on III-V Substrates
וווע טו			(Student) Monolithic III-V on LiNbO <sub>3</sub> for Nonlinear Optics Application
	Zezhi Wu	JU4	
30 pm	Zezhi Wu Jarod Mever	J04 J05	
30 pm 50 pm	Jarod Meyer	J05	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs
30 pm 50 pm : Energ	Jarod Meyer  gy Materials and Devices	J05	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree
30 pm 50 pm : <b>Ener</b> 50 pm	Jarod Meyer  gy Materials and Devices  Etee Kawna Roy	J05 K01	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree  (Student) Photovoltaic Characteristics of PERC-Like CdTe Solar Cells
30 pm 50 pm : Energ 50 pm 10 pm	Jarod Meyer  gy Materials and Devices  Etee Kawna Roy  Intuon Chatratin	J05 K01 K02	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree  (Student) Photovoltaic Characteristics of PERC-Like CdTe Solar Cells  (Student) Compensation Centers in Group-V Doped CdTe
30 pm 50 pm : Energ 50 pm 10 pm 30 pm	Jarod Meyer  gy Materials and Devices  Etee Kawna Roy  Intuon Chatratin  Stephen Polly	J05 K01 K02 K04	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree  (Student) Photovoltaic Characteristics of PERC-Like CdTe Solar Cells  (Student) Compensation Centers in Group-V Doped CdTe  InGaAs/GaAsP Multiple Quantum Well Enhanced Multijunction Photovoltaics
30 pm 50 pm : Energ 50 pm 10 pm 30 pm 50 pm	Jarod Meyer  gy Materials and Devices  Etee Kawna Roy  Intuon Chatratin	J05 K01 K02	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree  (Student) Photovoltaic Characteristics of PERC-Like CdTe Solar Cells (Student) Compensation Centers in Group-V Doped CdTe InGaAs/GaAsP Multiple Quantum Well Enhanced Multijunction Photovoltaics Improved AC Field Hall Measurements Using Hybrid Filters
30 pm 50 pm : Energ 50 pm 10 pm 30 pm 50 pm 10 pm	Jarod Meyer  gy Materials and Devices  Etee Kawna Roy Intuon Chatratin  Stephen Polly Jeffrey Lindemuth	K01 K02 K04 K05	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree  (Student) Photovoltaic Characteristics of PERC-Like CdTe Solar Cells (Student) Compensation Centers in Group-V Doped CdTe InGaAs/GaAsP Multiple Quantum Well Enhanced Multijunction Photovoltaics Improved AC Field Hall Measurements Using Hybrid Filters  BREAK
30 pm 50 pm 4: Energ 50 pm 10 pm 30 pm 10 pm 10 pm 30 pm	gy Materials and Devices Etee Kawna Roy Intuon Chatratin Stephen Polly Jeffrey Lindemuth Navid Attarzadeh	K01 K02 K04 K05	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree  (Student) Photovoltaic Characteristics of PERC-Like CdTe Solar Cells (Student) Compensation Centers in Group-V Doped CdTe  InGaAs/GaAsP Multiple Quantum Well Enhanced Multijunction Photovoltaics Improved AC Field Hall Measurements Using Hybrid Filters  BREAK (Student) Doped Ternary and Quaternary Transition-Metal Chalcogenides Electrocatalyst for Efficient Water Splitting
:10 pm :30 pm :50 pm <b>(: Enery</b> :50 pm :10 pm :30 pm :10 pm :30 pm :30 pm :30 pm :30 pm :30 pm :30 pm	Jarod Meyer  gy Materials and Devices  Etee Kawna Roy Intuon Chatratin  Stephen Polly Jeffrey Lindemuth	K01 K02 K04 K05	(Student) Room Temperature Photoluminescence at 3–8 µm in Epitaxial PbSe-SnSe Alloy Films on GaAs  UC, State Stree  (Student) Photovoltaic Characteristics of PERC-Like CdTe Solar Cells (Student) Compensation Centers in Group-V Doped CdTe InGaAs/GaAsP Multiple Quantum Well Enhanced Multijunction Photovoltaics Improved AC Field Hall Measurements Using Hybrid Filters  BREAK

## **WEDNESDAY PM**

	nic and Hybrid Materials f		
1:30 pm	Mohammad Ashif Hossain Chowdhury	L01	(Student) Monitoring Stability of Metal-Halide Perovskites Under Combined Stressors of Ion-Beam and Heat
:50 pm	Jonghoon Lee	L02	(Student) Bulk Incorporation of Organic Molecular Dopants into Two-Dimensional Ruddlesden-Popper Hybrid Perovskite Structures
2:10 pm	Yongsup Park	L03	Direct Measurements of HOMO-LUMO Transport Gaps at the Surface and Interface of Organic Semiconductor Materials Using Direct and Inverse Photoemission Spectroscopies (UPS & IPES)
2:30 pm	Andrew Herzing	L04	(Late News) Structural and Morphological Characterization of Organic Electrochemical Transistors via Four-Dimensional (4D) Scanning Transmission Electron Microscopy
2:50 pm	Shang-Hsuan Wu	L05	(Student, Late News) Climate-Adaptive Thermochromic Perovskite Smart Window Structures
3:10 pm			BREAK
M: Groւ	up III-Nitrides—Optical Em	itters	UC, Santa Barbara Harb
1:30 pm	Shigefusa F. Chichibu	M01	Short-Term Degradation Mechanisms of 275-nm-Band AlGaN-Based Deep-Ultraviolet Light Emitting Diodes Fabricated on a Sapphire Substrate
1:50 pm			(Student) Demonstration of AlGaN Tunnel Junction p-Down UV Light Emitting Diodes
2:10 pm			
2:30 pm	Matt Brubaker	M04	Shadowing Effects in Core-Shell InGaN Quantum Wells Grown on N-Polar GaN Nanowire Arrays by Molecular Beam Ep
2:50 pm	Anand Ithepalli	M05	(Student) Fabrication and Characterization of Epitaxially Grown and Lifted off AIN Membranes
3:10 pm			BREAK
3:30 pm	Mateusz Hajdel	#M06	(Student) III-Nitride Laser Diodes with Wide Quantum Wells: Influence of Built-In Electric Fields on the Light Generation Process
3:50 pm	Gordon Schmidt	M07	Advanced Cathodoluminescence Microscopy of a Cascaded InGaN/GaN LED
4:10 pm	Guangying Wang	M08	(Student) MOCVD of a Novel InGaN/GaN/AlGaN Active Region Design for Ultraviolet Light-Emitting Diodes
1:30 pm	Greg Muziol	M09	Critical Thickness of InGaN Grown by Plasma-Assisted Molecular Beam Epitaxy
4:50 pm	James Loveless	M10	(Student) Demystifying Light Extraction Efficiency in AlGaN Based UV LEDs
N: Char	racterization of Gallium Ox	cide-Ba	sed Materials and Devices I MCC, MCC Thea
1:30 pm	Hemant Jagannath Ghadi	N01	Evidence of Electron and Hole Photoemission During DLOS Characterization of Nitrogen Implanted $\beta$ -Ga $_2$ O $_3$
1:50 pm	Makoto Kasu	N02	Killer Defects Responsible for Leakage Current in HVPE (001) β-Ga <sub>2</sub> O <sub>3</sub> SBD Observed by Emission Microscopy and Synchrotron X-Ray Topography
2:10 pm	Takuya Maeda	N03	Photocurrent Induced by Franz-Keldysh Effect in β-Ga <sub>2</sub> O <sub>3</sub> Schottky Barrier Diode Under High Reverse Bias Voltage
2:30 pm	Dinusha Herath Mudiyanselage	N04	(Student) Anisotropic Electronic Properties of NiOx/β-Ga <sub>2</sub> O <sub>3</sub> p-n Heterojunctions on (-201), (001), and (010) β-Ga <sub>2</sub> O <sub>3</sub> Substrates
2:50 pm	Joe F. McGlone	N05	Impact of Radiation Damage and Buffer Charge on Si δ-Doped β-Ga <sub>2</sub> O <sub>3</sub> MESFETs
3:10 pm			BREAK
3:30 pm	Kenny Huynh	N06	Origin of Surface Defects in Homoepitaxially Grown (010) $\beta$ -Ga $_2$ O $_3$ Films
3:50 pm	Hsien-Lien Huang	#N07	(Student) Atomic Scale Defect Formation and Phase Transformation in Si Implanted β-Ga <sub>2</sub> O <sub>3</sub>
:10 pm	Michael Scarpulla	N08	Measuring Diffusion of Al, Sn, and Fe in $Ga_2O_3$ Using $\beta$ -(Al, $Ga)_2O_3$ / $Ga_2O_3$ Superlattices
4:30 pm	Minhan Lou	N09	Linearly Polarized UV, Blue and IR Photoluminescence from $\beta$ -Ga $_2$ O $_3$
1:50 pm	Cassandra Remple	N10	(Student) Photoluminescence Spectroscopy of Cr <sup>3+</sup> in β-Ga <sub>2</sub> O <sub>3</sub> and (Al <sub>0.1</sub> Ga <sub>0.9</sub> ) <sub>2</sub> O <sub>3</sub>
Student	t Finalists for Oral Present	ation A	ward – Part A (5:10 pm – 6:10 pm) UC, State Stre
	Frances Camille Masim Wu	#H07	(Student) Control of Dark Exciton Dynamics in Suspended WSe <sub>2</sub> Monolayer via Electrostatic Deflection
	Sushovan Dhara	#F01	(Student) [100] and [010] Oriented β-Ga <sub>2</sub> O <sub>3</sub> Trench Schottky Barrier Diodes with Improved On-Resistance Using Low Damage Atomic Ga Etching
	Ryoya Ishikawa	#S01	(Student) Anisotropic Electron and Hole Mobilities in 4H-SiC Bulk Crystals
	Ashlee Garcia	#GG03	(Student) SiO <sub>2</sub> Surface Planarization for Molecular Beam Epitaxy Selective Area Regrowth of High Aspect Ratio Microstructures
	Hsien-Lien Huang	#N07	(Student) Atomic Scale Defect Formation and Phase Transformation in Si Implanted β-Ga <sub>2</sub> O <sub>3</sub>
Student	t Finalists for Oral Present	ation A	ward-Part B (5:10 pm-6:10 pm) UC, Lobe
	Jingxian Li	#Z01	(Student) Origins of Nonvolatility in Resistive Switching Memory
	Aaron Engel	#C04	(Student) Molecular Beam Epitaxy of Strained Superlattice InAlGaAs/AlGaAs Spin-Polarized Photocathodes
	1		(Student) Multi-Weight Magnetic Artificial Synapses with Geometry-Dependent Neuromorphic Functionality
	Thomas Leonard	#Z06	(Student) Multi-Weight Magnetic Artificial Synapses with decimenty-Dependent Neuromorphic Functionality
	Thomas Leonard Mateusz Hajdel	#Z06 #M06	(Student) III-Nitride Laser Diodes with Wide Quantum Wells—Influence of Built-In Electric Fields on the Light Generation Process

## **POSTER SESSION**

### WEDNESDAY PM | LAGOON PLAZA

#### **General Viewing**

Wednesday 3:10 pm – 3:30 pm Poster Session

6:00 pm - 8:00 pm

Thursday 10:00 am - 10:20 am 3:10 pm - 3:30 pm

### **Poster Set-up**

Wednesday, 9:30 am - 3:00 pm

#### **Poster Tear Down**

Thursday, no later than 5:30 pm

Remaining posters will be discarded.

Poster presenters should be standing with their poster.

Student poster presenters must attend from 6:00 pm to 8:00 pm to present poster and answer questions to be eligible for the Best Student Poster Presentation Award.

Presenter	Paper #	Title
Durga Paudyal	PS01	Distinguishing Erbium Dopants in Y <sub>2</sub> O <sub>3</sub> by Site Symmetry—Ab Initio Theory of Two Spin-Photon Interfaces
Andrew Christopher Grizzle	PS02	(Student) Molecule Spin State and Molecular Structure Impact on Molecular Spintronics Device Properties
Sanghun Lee	PS03	Fabrication of Ohmic Contact on Sulfurized Copper-Doped ZnS
Macarena Maria Santillan	PS04	(Student) Persistent Photoconductivity of Potassium Tantalate ${\rm KTaO_3}$
Yoshitha Hettige	PS05	(Student) Optical Constants and Lattice Vibrations of Bulk SrTiO <sub>3</sub> and BaSnO <sub>3</sub> Using Spectroscopic Ellipsometry from 0.03-6.5 eV
Wen-Chang Huang	PS06	Impact of Oxygen Addition on Enhancing Electrochromic Performance of Vanadium Pentoxide Film by Sputtering
Wen-Chang Huang	PS07	Effect of Cu Doping on ZnO Based Thin-Film Sensor for Hydrogen Sensing
M. Jasim Uddin	PS08	Surface Modified ZnSnO <sub>3</sub> Hollow Nanorod/PDMS Based Piezoelectric Nano-Generator for Harvesting Mechanical Energy
Efracio Mamani Flores	PS09	Thermoelectric Properties Study on the Ferroelectric Materials BiFeO <sub>3</sub> and Bi <sub>2</sub> FeCrO <sub>6</sub> via First Principles
Omid Dadras-Toussi	PS10	3D-Printing of Organic Bioelectronics and Biosensors
Wen-Shiung Lour	PS11	Layered Processes for InGaP/GaAs Heterojunction Bipolar Transistors with a Buried-Base Contact
Takashi Tsukasaki	PS12	Suppression of Nitrogen Composition Fluctuation by Beryllium Doping in GaAsN Ternary Alloys
Zinah M Alsaad	PS13	(Student) Optimization of the Event-Based Sensor's Photoreceptor Circuit for Mid-Wave Infrared Photodetection
Enbo Yang	PS14	(Student) Mass Spectroscopic Investigation on Reactions of Tin Tetrachloride and Germane for SiGeSn Chemical Vapor Deposition Growth
Geonwook Yoo	PS15	Reactive-Sputtering and Ferroelectric Switching of Aluminum Scandium Nitride on (-201)β-Ga <sub>2</sub> O <sub>3</sub> Substrates
Min-Yeong Kim	PS16	(Student) Imaging ${\rm Ga_2O_3}$ Defects and Determining Its Influence on Electrical Properties
Paul Gaurav G. Nalam	PS17	Fabrication and Characterization of High Quality Rutile-Phase ${\rm GeO}_2$ Films on MgO(100) for Application in Optoelectronics
Francelia Sanchez Escobar	PS18	Growth Optimization of Sn-Doped Gallium Oxide Thin Films on Sapphire for Deep UV Photodetectors with Ultrafast Response
Sameer Kumar Mallik	PS19	(Student) Thermally-Driven Multi-Level Non-Volatile Memory in Monolayer MoS <sub>2</sub> Field-Effect Transistors
Ramesh G. Mani	PS20	The Effect of Current Annealing on the Transport Properties of CVD Graphene
Changkai Yu	PS21	(Student) Two-Dimensional Hole Gases in N-Polar AlGaN/GaN Heterostructures Grown on GaN Bulk Substrates
Mihee Ji	PS22	Dependence of Compositional Inhomogeneity and Thermal Conductivity on Growth Conditions of High-Al-Content AlGaN Alloys Grown by High Temperature Plasma-Assisted Molecular Beam Epitaxy
Hirandeep Reddy Kuchoor	PS23	Axial Configured GaAsSb Ensemble Nanowire-Based p-i-n photodetectors up to 1.1 $\mu m$
Tae Kyoung Kim	PS24	Impact of Current Stress on the Optoelectronic Performances in GaN-Based Micro-LEDs
Nobuo Sasaki	PS25	Motion of a Void Induced by Agglomeration at the Solid-Liquid Interface in the Continuous-Wave Laser Crystallization
Yura Seo	PS26	(Student) Effect of the Atomic Arrangement at the Apex of Tip on AFM Atomic Lattice Images
Dominique Newell	PS27	(Student) Wavelength Dependence of the Verdet Constant Using Visible LEDs and a Modified Pulsed Magnet Station
Jialin Wang	PS28	(Late News) Design and Fabrication of a Fully Epitaxially Grown AIScN FBAR
Rahima Nasrin	PS29	Influence of Cobalt Doping on Surface Morphology, Structural and Optical Behavior of ZnO Nanoparticles Synthesized by CBD Technique
Madison Suzanne King	PS30	(Student) High Dielectric Microdroplet Whispering Gallery Mode Resonators for Opto-Electronics
Pius Suh	PS31	Covalently Connected Single-Molecule Magnets on the Exposed Edges of a Nickel Ferromagnetic Electrode-Based Magnetic Tunnel Junction
Nurdan Mese	PS33	(Student) Electrochemical and Morphological Properties of PEDOT with Various Boron-Containing Dopants

## **POSTER SESSION**

#### WEDNESDAY PM | LAGOON PLAZA

Presenter	Paper #	Title
Julia Isidora Salas Toledo	PS34	(Student) Energy Harvesting with Thermoplastic Polyurethane Nanofiber Mat Integrated with Functionalized Multiwalled Carbon Nanotubes
Hyerin Jo	PS35	(Student) ZnO TFTs Property with Photoelectric Synaptic Devices
Shea Tonkinson	PS36	(Student) Synthesis and Characterization of CsPbBr <sub>3</sub> Perovskites for Radiation Detection Applications
Nolan T. Herbort	PS37	(Student) Synthesis and Characterization of Pulsed-Laser Deposited Ba(Fe $_{0.7}$ Ta $_{0.3}$ )0 $_3$ - $\delta$ Thin Films
Eyasu Ajebe	PS39	Synergistic Effect of Combining UIO-66 and Mxene Nanosheets in Pebax Mixed Matrix Membranes for CO <sub>2</sub> Capture and Separation
Sherman Peek	PS40	(Student) Femtosecond Laser Processing on Bulk Materials with Water-Assisted Debris Removal
Jeonghum Woo	PS41	Micro Probe System for In Situ X-Ray Scattering
Mehrdad Jalali	PS42	Information Visualization in Materials Science through Social Networks Modeling
Seoyeo Park	PS43	(Student, Late News) Metallic Fusion-Induced Flexible Nanocrystal Thin Films for High-Performance Electromagnetic Interference Shielding Materials
Hansel Hobbie	PS44	(Student, Late News) Zirconium Oxide Dielectric Thin Films Fabricated by Water-only Aerosol Jet Printing
Takumi Ikenoue	PS45	(Late News) Epitaxial Growth of Lattice-Matched NiMgZnO Films on MgO Substrate via Mist Chemical Vapor Deposition
Shisong Luo	PS46	(Student, Late News) High-Performance hBN/Graphene/AlGaN/GaN Hot Electron Transistors
Brittany Smith	PS47	(Student, Late News) Realizing 3D Microstructures from Graphene Using Aerosol Jet Printing
Ji-Hyuk Choi	PS48	(Late News) Designing Surface Chemistry of Semiconductor Nanocrystals for High-Performance Thin-Film Transistors
Yi-Kuan Chen	PS49	(Student, Late News) Pyridine-Carbonitriles-Based Thermally Activated Delayed Fluorescence Emitters for High Performance OLEDs
Stephanie Rouamba	PS51	(Student, Late News) Modeling Effect of Perovskite Layer on Efficiency and Development of Efficient and Stable Perovskite Layer
Shadi Omranpour	PS52	(Student) Photocathode Characteristics Dependency on Mg Incorporation in (N-polar) Semi-Polar and Non-Polar 3D Microstructures by Selective Area Epitaxy

## Journal of Electronic Materials

A special issue of the *Journal of Electronic Materials (JEM)*\* will be published with peer-reviewed papers from the 65th Electronic Materials Conference.

- Article submission date is September 30, 2023 at 11:59 pm (ET)
- Contact the 2023 Special Issue Editors listed below.

The *Journal of Electronic Materials* reports monthly on the science and technology of electronic materials, while examining new applications for semiconductors, magnetic alloys, dielectrics, nanoscale materials and photonic materials. The *Journal* welcomes articles on methods for preparing and evaluating the chemical, physical, electronic and optical properties of these materials. Specific areas of interest are materials for state-of-the-art transistors, nanotechnology, electronic packaging, detectors, emitters, metallization, superconductivity and energy applications. Review papers on current topics enable individuals in the field of electronics to keep abreast of activities in areas peripheral to their own.

Manuscripts for the EMC 2023 collection will be evaluated according to the same high standards as would be applied to any article submitted to the *Journal*. Authors are encouraged to read carefully and comply with the "Instructions for Authors" on **springer.com/journal/11664**. Submission of a manuscript implies that the work described has not been previously published and is not under consideration for publication elsewhere.

#### **Questions?**

Contact the 2023 Special Issue Editors:

Jennifer Hite

Jennifer.hite@nrl.navy.mil

Nadeem Mahadik

nadeem.mahadik@nrl.navy.mil

Parsian Mohseni

pkmohseni@rit.edu

Jamie Phillips iphilli@udel.edu

Shadi Shahedipour-Sandvik

sshahedipour-sandvik@sunypoly.edu

**Randy Tompkins** 

randy.p.tompkins.civ@mail.mil



\* A journal of The Minerals, Metals & Materials Society (TMS). Editor-in-Chief—Shadi Shahedipour-Sandvik

#### **THURSDAY AM**

O: Group	lll-Nitrides—Novel Ni	tride G	rowth Music Building, Lotte Lehmann
8:20 am	Matthew Hardy	001	Epitaxial Growth of High ScN Fraction ScAIN on NbN/SiC and SiC
8:40 am	Ding Wang	002	Epitaxial Ferroelectric ScAIN—Thickness Scaling to the Nanometer Scale
9:00 am	Naomi Pieczulewski	003	(Student) Atomic Structure of β-Nb <sub>2</sub> N/AIN/ β-Nb <sub>2</sub> N Epitaxial Josephson Junction
9:20 am	Swarnav Mukhopadhyay	004	(Student) First Demonstration of C-Doped Semi-Insulating N-Polar GaN Using Propane Precursor
9:40 am	Vincent E. Meyers	005	(Late News) Growth of High-Quality Ga-Polar GaN Growth on Mixed-Polarity AIN
10:00 am			BREAK
10:20 am	Alexander Austin Chaney	006	Metal Modulated Epitaxy Growth of AIN/GaN Short Period Superlattices with Individual Layer Thicknesses Less Than 2 nm
10:40 am	Christopher M. Matthews	007	(Student) Surface Oxide Removal on AIN Substrates via Low Temperature Aluminum Flashing
11:00 am	Mohammad Hussain	008	High Figure of Merit Extreme Bandgap Al <sub>0.87</sub> Ga <sub>0.13</sub> N-Al <sub>0.64</sub> Ga <sub>0.38</sub> N Heterostructures Over Bulk AlN Substrates
11:20 am	Clarence Y. Chan	009	(Student) Mechanism of hv-MacEtch in GaN and III-Nitrides Heterojunctions
11:40 am	Chandrashekhar Prakash Savant	010	(Student) MBE Growth, Characterization of BAIN Films and 2D Electron Gas in Epitaxial BAIN/GaN Heterojunction
P: 2D Ma	aterials Synthesis and	Charac	terization UC, Corwin East
8:20 am	Thomas Virgil McKnight	P01	(Student) Spectroscopic Ellipsometry for <i>In Situ</i> Monitoring of MoS <sub>2</sub> Growth at the Sub-Monolayer Limit
8:40 am	Chen Chen	P02	Effects of Growth Temperature on the Properties of Wafer-Scale Epitaxial MoS <sub>2</sub> Monolayers Grown by Metalorganic Chemical Vapor Deposition
9:00 am	Meghan Leger	P03	(Student) MOCVD Growth and Characterization of MoSe <sub>2</sub> Nanodots within a WSe <sub>2</sub> Monolayer Matrix
9:20 am	Ramesh G. Mani	P04	Study of Single Crystal Graphene Grown by Chemical Vapor Deposition on Copper
9:40 am	Yeoseon Sim	P05	(Late News) Oxidation Mechanism of 2H-MoTe2 at the Atomic Scale
10:00 am			BREAK
10:20 am	Michael Pedowitz	P06	(Student) Transformation to Alkali Birnessites via Simple Intercalation of Electrochemically Grown 2D-Layered H-Type Manganese Dioxide on Epitaxial Graphene
10:40 am	Shigefusa Chichibu	P07	Ultraviolet Luminescence Dynamics of Hexagonal BN Epilayers Grown by Chemical Vapor Deposition Using Carbon-Free Precursors
11:00 am	Shubham Mondal	P08	(Student) Epitaxial Growth of Wafer-Scale Monolayer Hexagonal Boron Nitride (hBN)
Q: Optic	al Materials on Si		UC, Flying A Studios
8:20 am	Ellie Yilien Wang	Q01	(Student) Growth and Characterization of Al <sub>x</sub> In <sub>1-x</sub> As <sub>y</sub> Sb <sub>1-y</sub> Digital Alloys on InP on Si
8:40 am	Alexandria Ragsdale	Q02	(Student) Synthesis and Characterization of AISb for Growth on Si and Integrated Circuit Based Radiation Detection
9:00 am	Hyun Uk Chae	Q03	(Student) Defect Filtering at the Interface of MOCVD/TLP Heterogenous Epitaxial III-V on Silicon
9:20 am	Joshua Cooper	Q04	Mechanisms for Solute Incorporation in Highly Mismatched Ge <sub>1-x-y</sub> Sn <sub>x</sub> C <sub>v</sub> Alloys
9:40 am	Amanda N. Lemire	Q05	(Student) Doping and Surfactant Behavior of Antimony in Molecular Beam Epitaxy Grown Germanium-Tin
10:00 am			BREAK
R: Epita	kial Materials Design a	nd Pro	perties UC, Flying A Studios
10:40 am	Rithvik Ramesh	R01	(Student) Engineering of the Interband Second Order Optical Nonlinearity with Asymmetric Coupled Quantum Wells
11:00 am	Qian Meng	R02	(Student) Atom Rearrangement in BGa(In)As Alloys Under Annealing
11:20 am	Subha Prakash Mallick	R04	(Student) The Effect of Group-V "Blow-by" on the Structural and Optical Properties of Al <sub>x</sub> In <sub>1-x</sub> As <sub>y</sub> Sb <sub>1-y</sub> Digital Alloys Grown by Molecular Beam Epitaxy
11:40 am	Mina Moradnia	R05	(Student) Composition Control of Ternary Group-IIIa-IIIb-Nitride Alloy by Hybrid Chemical Vapor Deposition— A Thermodynamic Analysis

# Student Finalist for Oral Presentation





#### **CONFERENCE BADGE**

Badges must be worn at all times within the Conference venue, including all receptions.

#### **RECORDING/PHOTO POLICY**

Recording or photographing Conference presentations, posters or displays is strictly prohibited without prior permission of the presenter.

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### THURSDAY AM

	laterial Characterization	on, Proc	cessing and Devices UC, State Stree	
3:20 am	Ryoya Ishikawa	#S01	(Student) Anisotropic Electron and Hole Mobilities in 4H-SiC Bulk Crystals	
8:40 am	Zeyu Chen	S02	(Student) Ray Tracing Simulation of Defects of 4H-SiC in 22-4 16 Reflection of Synchrotron Monochromatic Beam X-Ray Topography in Grazing Incident Geometry	
9:00 am	Qianyu Cheng	S03	Analysis of Distribution of Threading Edge Dislocation Low Angle Grain Boundaries in 4H-SiC Wafers through Synchrotron X-Ray Topography	
9:20 am	Shanshan Hu	S04	Investigation of Defect Formation During Initial Stage of PVT-Grown 4H-SiC Crystals	
9:40 am	Scott Galen Criswell	S05	(Student) Nanoscale Spectroscopy of Extended Defects in 4H Silicon Carbide	
10:00 am			BREAK	
10:20 am	Michael Evan Liao	S06	Mitigation of Basal Plane Dislocation Faulting in 4H-SiC Buffer Layers Using Channeled Vanadium Implantation	
10:40 am	Suman Das	S08	Study of Dopant Activation and Ionization for Phosphorus in 4H-SiC	
11:00 am	Jiashu Qian	S09	(Student) A Comparison of Body Diode Degradation in Commercial 1.2 kV SiC Power MOSFETs with the Planar and Trench Structure	
11:20 am	Nadeemullah Mahadik	S10	Reliability of Room Temperature vs High Temperature Implantation in 3.3kV SiC MOSFETs	
11:40 am	Ludovico Megalini	S07	Advanced Carbon Film as a Superior C- Cap for SiC devices	
T: Organ	nic Devices and Molec	ular Ele		
8:20 am	Pawan Tyagi	T01	Single-Molecule Magnet (SMM) Internal Atomic Configuration Impact of Ferromagnetic Layers of Magnetic Tunnel Junction—A Monte Carlo Study	
8:40 am	Brian S. Rolczynski	T02	Understanding Electronic Energy Transport in DNA-Scaffolded Molecular Networks Using Machine-Learning Methods	
9:00 am	Libin Liang	T03	(Student) Strain-Enhanced Formation of 1D Coherent Exciton-Polaron States in Small Molecule Semiconductors	
9:20 am	Jung Sun Eo	T04	(Student) Effect of Molecular Tilt Configuration in Molecular Heterojunction with Two-Dimensional Semiconductor	
9:40 am	Phong Nguyen	T05	(Student) Surface-Confined Brønsted Acidic Doping of Conjugated Polymers Thin Films	
10:00 am	Thong regayon	100	BREAK	
10:20 am	Chankeun Yoon	T07	(Student) Advantages of Adding a Weak Second Gate in Sub-Micron Bottom-Contact Organic Thin-Film Transistors	
0:40 am	Ramin Karimi Azari	T08	(Student) Effect of Thickness and Molecular Weight of Poly (3-hexylthiophene) Film on Ion-Gated Transistor Response Tin	
10.40 aiii	Maiiiii Naiiiii Azaii	100	and Synaptic Functions	
11:00 am	Amrita Chakraborty	T09	(Student) Manufacturing of Highly Conductive Organic PEDOT:PSS Films for Electronic Devices	
11:20 am	Sarah L. Swisher	T10	(Late News) Transparent, Inkjet-Printed PEDOT:PSS Electrotrode Arrays for Large-Area Multimodal Neural Interfaces	
U: Grou	p III-Nitrides—Contact	s and S	pecial Topics UC, Santa Barbara Harbo	
8:20 am	Shivali Agrawal	U01	(Student) Ohmic Contacts to Homoepitaxial Ultrawide Bandgap n-AlGaN Grown on Bulk AlN Substrates	
3:40 am	Amit P. Shah	U02	Evolution of Surface Microstructure of Re-Al-Ni-Au Based Ohmic Contacts on N-Type GaN	
9:00 am	Mafruda Rahman	U03	(Student) Ultrawide Bandgap Optoelectronic Properties of Single Crystal Bulk AIN and Sapphire/AIN Templates	
9:20 am	Haotian Xue	U04		
			Structural and Optical Characterization of Thin AllnN Films on c-Plane GaN Substrates  Nano-Scale Correlation of Real Structure, Band Bending and Local Electric Fields in the Narrow pn+ Regions of a	
7.4U ain	Juergen Christen	U05	Nano-Scale Correlation of Real Structure, Band Bending and Local Electric Fields in the Narrow pn+ Regions of a GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization	
9:40 am 10:00 am	Juergen Christen	U05		
	Juergen Christen Alireza Lanjani	U05 U06	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization	
10:00 am 10:20 am			GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector by MOCVD for Near IR Range	
10:00 am 10:20 am 10:40 am	Alireza Lanjani	U06	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector	
10:00 am 10:20 am 10:40 am 11:00 am	Alireza Lanjani Guangying Wang	U06 U07	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector by MOCVD for Near IR Range  (Student) InGaN Films on Crystalline ScAIMgO <sub>4</sub> on Al <sub>2</sub> O <sub>3</sub> Substrates by MOCVD with up to 123 nm PL Redshift	
10:00 am 10:20 am 10:40 am 11:00 am	Alireza Lanjani Guangying Wang Geoffrey Foster	U06 U07 U08	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector by MOCVD for Near IR Range  (Student) InGaN Films on Crystalline ScAIMgO <sub>4</sub> on Al <sub>2</sub> O <sub>3</sub> Substrates by MOCVD with up to 123 nm PL Redshift Characterization of Optically Modulated Semi-Insulating GaN Photoconductive Semiconductor Switches  Piezoelectric Sensing in Extreme Environments Using Flexible Ultrawide Bandgap III-N Thin Films	
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10:00 am 10:20 am 10:40 am 11:00 am 11:20 am 11:40 am <b>/: Grow</b> 3:20 am	Alireza Lanjani Guangying Wang Geoffrey Foster Nam-In Kim Yinxuan Zhu th of Gallium Oxide and Zhuoqun Wen Jacob Steele	U06 U07 U08 U09 U10 d Other V01 V02	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector by MOCVD for Near IR Range  (Student) InGaN Films on Crystalline ScAIMgO $_4$ on Al $_2$ O $_3$ Substrates by MOCVD with up to 123 nm PL Redshift Characterization of Optically Modulated Semi-Insulating GaN Photoconductive Semiconductor Switches Piezoelectric Sensing in Extreme Environments Using Flexible Ultrawide Bandgap III-N Thin Films  (Student, Late News) Demonstration of 0.7 $\Omega$ .mm MOCVD-Grown Reverse Graded Contacts on Al $_0$ 8, Ga $_0$ 1, N Channel  Ultrawide-Bandgap Oxides  MCC, MCC Theater (Student) Si Doping of $\beta$ -Ga $_2$ O $_3$ by Disilane via Hybrid Plasma-Assisted Molecular Beam Epitaxy  (Student) Epitaxial Growth of $\alpha$ -(Al $_3$ Ga $_1$ 2, O $_3$ 3 by Suboxide Molecular-Beam Epitaxy at 1 $\mu$ m/h	
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10:00 am 10:20 am 10:20 am 11:00 am 11:20 am 11:40 am 20:20 am 3:40 am 9:20 am 9:20 am 9:40 am 10:00 am	Alireza Lanjani Guangying Wang Geoffrey Foster Nam-In Kim Yinxuan Zhu  th of Gallium Oxide and Zhuoqun Wen Jacob Steele Brenton A. Noesges Abishek Katta Fikadu Alema	U06 U07 U08 U09 U10 <b>d Other</b> V01 V02 V03 V04 V05	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector by MOCVD for Near IR Range  (Student) InGaN Films on Crystalline ScAIMgO $_4$ on Al $_2O_3$ Substrates by MOCVD with up to 123 nm PL Redshift  Characterization of Optically Modulated Semi-Insulating GaN Photoconductive Semiconductor Switches  Piezoelectric Sensing in Extreme Environments Using Flexible Ultrawide Bandgap III-N Thin Films  (Student, Late News) Demonstration of 0.7 $\Omega$ .mm MOCVD-Grown Reverse Graded Contacts on Al $_{0.86}$ Ga $_{0.15}$ N Channel  Ultrawide-Bandgap Oxides  MCC, MCC Theate  (Student) Si Doping of $\beta$ -Ga $_2O_3$ by Disilane via Hybrid Plasma-Assisted Molecular Beam Epitaxy  (Student) Epitaxial Growth of $\sigma$ -(Al $_x$ Ga $_{1-x}$ ) $_2O_3$ by Suboxide Molecular-Beam Epitaxy at 1 $\mu$ m/h  Optimizing Si Dopant Control in n-type $\beta$ -Gallium Oxide  Demonstration of MOCVD Based In Situ Ga Etching of $\beta$ -Ga $_2O_3$ Using TEGa  Controllable Doping of MOCVD Ga $_2O_3$ with Nitrogen Using Ammonia Precursor  BREAK	
10:00 am 10:20 am 10:40 am 11:00 am 11:20 am 11:40 am	Alireza Lanjani Guangying Wang Geoffrey Foster Nam-In Kim Yinxuan Zhu th of Gallium Oxide and Zhuoqun Wen Jacob Steele Brenton A. Noesges Abishek Katta	U06 U07 U08 U09 U10 d Other V01 V02 V03 V04	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector by MOCVD for Near IR Range  (Student) InGaN Films on Crystalline ScAIMgO <sub>4</sub> on Al <sub>2</sub> O <sub>3</sub> Substrates by MOCVD with up to 123 nm PL Redshift  Characterization of Optically Modulated Semi-Insulating GaN Photoconductive Semiconductor Switches  Piezoelectric Sensing in Extreme Environments Using Flexible Ultrawide Bandgap III-N Thin Films  (Student, Late News) Demonstration of 0.7 $\Omega$ .mm MOCVD-Grown Reverse Graded Contacts on Al <sub>0.86</sub> Ga <sub>0.15</sub> N Channel  **Ultrawide-Bandgap Oxides**  MCC, MCC Theate  (Student) Si Doping of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> by Disilane via Hybrid Plasma-Assisted Molecular Beam Epitaxy  (Student) Epitaxial Growth of $\sigma$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> by Suboxide Molecular-Beam Epitaxy at 1 $\mu$ m/h  Optimizing Si Dopant Control in n-type $\beta$ -Gallium Oxide  Demonstration of MOCVD Based In Situ Ga Etching of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Using TEGa  Controllable Doping of MOCVD Ga <sub>2</sub> O <sub>3</sub> with Nitrogen Using Ammonia Precursor  BREAK  Vertically Aligned $\beta$ -Ga <sub>2-x</sub> W <sub>x</sub> O <sub>3</sub> Nanocomposites for Ultrafast Deep-UV Photodetectors  (Student) Investigation of Phase Transition and Bandgap Engineering in (Mg <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> Thin Films Grown	
10:00 am 10:20 am 10:20 am 11:00 am 11:20 am 11:40 am V: Grow 3:20 am 3:40 am 9:00 am 9:40 am 10:00 am 10:00 am	Alireza Lanjani Guangying Wang Geoffrey Foster Nam-In Kim Yinxuan Zhu  th of Gallium Oxide and Zhuoqun Wen Jacob Steele Brenton A. Noesges Abishek Katta Fikadu Alema  Debabrata Das	U06 U07 U08 U09 U10  d Other V01 V02 V03 V04 V05	GaN Superjunction Using Highly Spatially Resolved STEM-CL Characterization  BREAK  (Student) Design and Optimization of Room Temperature AlGaN/GaN Multi Quantum Well Infrared Photodetector by MOCVD for Near IR Range  (Student) InGaN Films on Crystalline ScAIMgO4 on Al2O3 Substrates by MOCVD with up to 123 nm PL Redshift Characterization of Optically Modulated Semi-Insulating GaN Photoconductive Semiconductor Switches Piezoelectric Sensing in Extreme Environments Using Flexible Ultrawide Bandgap III-N Thin Films  (Student, Late News) Demonstration of 0.7 $\Omega$ .mm MOCVD-Grown Reverse Graded Contacts on Al086Ga015N Channel  Ultrawide-Bandgap Oxides  MCC, MCC Theate  (Student) Si Doping of $\beta$ -Ga2O3 by Disilane via Hybrid Plasma-Assisted Molecular Beam Epitaxy  (Student) Epitaxial Growth of $\alpha$ -(Al $_{\alpha}$ Ga1- $_{\alpha}$ )2O3 by Suboxide Molecular-Beam Epitaxy at 1 $\mu$ m/h  Optimizing Si Dopant Control in n-type $\beta$ -Gallium Oxide  Demonstration of MOCVD Based In Situ Ga Etching of $\beta$ -Ga2O3 Using TEGa  Controllable Doping of MOCVD Ga2O3 with Nitrogen Using Ammonia Precursor  BREAK  Vertically Aligned $\beta$ -Ga2- $_{\alpha}$ W $_{\alpha}$ O3 Nanocomposites for Ultrafast Deep-UV Photodetectors	

# Student Finalist for Oral Presentation

## THURSDAY PM

W: Grou	p III-Nitrides—Late N	ews	Music Building, Lotte Lehmani		
1:50 pm	Emma Rocco	W01	(Late News) Impact of Cap Layer Thickness on Ga- and N-Polar Microstructure Photocathodes		
2:10 pm	Md. Irfan Khan	W02	(Student, Late News) Investigation of Si Doping in N-Polar AIN by Plasma Assisted Molecular Beam Epitaxy		
2:30 pm	Georgios Doundoulakis	W03	(Late News) Nanometer-Resolution Piezoelectric Probing for Vertical Top-Down GaN Nanowire Field Emitter Devices with Integrated Leveling		
2:50 pm	Holger Eisele	W04	(Late News) Characterization of the Space-Charge Region of a GaN <i>pn</i> -Junction and <i>pin</i> -Drift-Diode Using EBIC and CL		
3:10 pm			BREAK		
X: Grou	III-Nitrides—Growth	and C	haracterization UC, Corwin Eas		
1:30 pm	Siddha Pimputkar	X01	Computational Fluid Dynamics Modeling of a Novel High-Pressure Spatial Chemical Vapor Deposition Reactor (HPS-CVD)		
1:50 pm	Yafei Liu	X02	Design for Growth of Indium-Containing Nitrides  Characterization of Growth Sectors in Patterned HVPE Gallium Nitride Substrate Wafers		
2:10 pm	Jack Almeter	X03	(Student) Wing Tilt in ELO-Grown GaN		
2:30 pm	Keisuke Motoki	X04	(Student) Structural Analysis and Observation of Tilts, Twists and Crystallographic Orientation of High-Quality, Metal Rich Grown Sc <sub>0</sub> , Al <sub>0</sub> , N		
2:50 pm	Andrew J. Winchester	X05	Microscale Surface Electronic Properties of Defects in Gallium Nitride Epitaxial Layers		
3:10 pm	Andrew C. Willeliestel	700	BREAK		
3:30 pm	Kohei Shima	X06	Luminescence Studies of Bulk GaN Crystals Grown by the Low-Pressure Acidic Ammonothermal Method		
3:50 pm	Seokje Lee	X07	(Student) Pulsed-Mode Metalorganic Vapor-Phase Epitaxial Growth of GaN on Graphene/c-Sapphire for Freestanding GaN Thin Films		
4:10 pm	Shubham Mondal	X08	(Student, Late News) Molecular Beam Epitaxy and Characterization of N-Polar AlGaN on C-Face 4H-SiC		
4:30 pm	Oguz Odabasi	X09	(Student) N-Polar GaN Deep Recess HEMTs with ALD HfO <sub>2</sub> as Gate Dielectric		
4:50 pm	Liang Qi	X10	Mechanisms for Polytype Selection During the Growth of Self-Catalyzed GaN Nanowires		
Y: Plasm	nonics, Photonics for	Detecti	ion and Emission UC, Flying A Studio		
1:30 pm	S. Maryam Vaghefi Esfidani	Y01	Critical Coupling in Phonon Polariton Organ Pipe Resonance for Infrared Sensing		
1:50 pm	Alexander Ware	Y02	(Student) Decoupling Mid-Wave Infrared Absorption and Long-Wave Infrared Radiative Cooling in Bolometric Elements		
2:10 pm	Minho Choi	Y03	Massively Degenerate Coherent Perfect Absorber Using a Single Optic		
2:30 pm	Wilder Acuna	Y04	(Student) Property Control of ErAs:InGaAlBiAs Materials for Terahertz Emitters and Detectors Pumped at 1550 nm		
2:50 pm	Brandon Swartz	Y05	(Student) Large-Scale Inversely Designed Metasurfaces for Broadband LWIR Optical Edge Detection		
3:10 pm			BREAK		
3:30 pm	Zizwe Chase	Y06	Flexible Metastructure Graded-Index Lens as a Quantum Algorithm Emulator		
3:50 pm	Haonan Ling	Y07	(Student) Taming Mid-IR Resonances with Hexagonal Boron Nitride		
4:10 pm	Madeline Brown	Y08	(Student) Topological Spin-Valley Coupling in 2D Photonic Crystals		
4:30 pm	Abhilasha Kamboj	Y09	(Late News) Localized Phonon Polariton Modes in GaN/AIN Nanowires		
4:50 pm	Md. Toriqul Islam	Y10	(Student, Late News) Prospects of Dilute Bismuth in InGaBiAs Alloys for e-SWIR Photodetectors		
Z: Emer	gent Materials and De	evices f	for Microelectronics UC, State Stree		
1:30 pm	Jingxian Li	#Z01	(Student) Origins of Nonvolatility in Resistive Switching Memory		
1:50 pm	Ramin Karimi Azari	Z02	(Student) Controlling Response Time and Synaptic Behavior of Ion-Gated Transistors Through Modulating Different Aspects of Input Biases		
2:10 pm	Solomon Amsalu Chekol	Z03	(Student) Effect of the Counter Electrode Material on the SET Kinetics of Ag/HfO <sub>2</sub> -Based Diffusive Memristors		
2:30 pm	Nithil Harris Manimaran	Z04	(Student) Realizing a Linear Synaptic Weight Update in Electric-Double-Layer Gated Transistors for Achieving Spike-Timing-Dependent Plasticity in Neuromorphic Computing		
2:50 pm	Mousam Charan Sahu	Z05	(Student) Highly Stable and Controllable Quantum Conductance States up to 100 G0 in TiO <sub>2</sub> Memristor		
3:10 pm			BREAK		
3:30 pm	Thomas Leonard	#Z06	(Student) Multi-Weight Magnetic Artificial Synapses with Geometry-Dependent Neuromorphic Functionality		
3:50 pm	Marzieh Savadkoohi	Z07	(Student) Impact of Single Molecule Magnets (SMM) on Magnetic Properties of a Cross-Junction-Shaped Magnetic Tunnel Junction		
4:10 pm	Finley Haines	Z08	(Student) Vertical Spin Valves Architectures Based on Screw Dislocations in Semiconductor Nanomembranes		
4:30 pm	Amrita Chakraborty	Z09	(Student) Methodology for Mitigation of the Reliability of a Resistive RAM Memory Array Caused by Thermal Cross-Talk Between the Memory Cells		
4:50 pm	Kuan-Hao Chiao	Z10	(Student) Micromagnetic Simulations for Deterministic Switching in SOT-MRAM Cell with Additional Heavy Metal Capping Strip		

<sup>#</sup> Student Finalist for Oral Presentation

### THURSDAY PM

AA: Sem	niconducting Oxide Th	nin Film	s and Transistors	UC, Lobero
1:50 pm	Farida Selim	AA02	Atomic Layer Deposition of Highly Conductive Highly Transparent Indium Gallium Doped Zinc Oxide T	hin Films
2:10 pm	Camilo Velez Cuervo	AA03	Atomic Layer Deposition (ALD) and Sol-Gel Techniques Comparison from the Perspective of TiO <sub>2</sub> Thin	-Films Fabrication
2:30 pm	Eli Powell	AA04	(Student) Donor Activation in Boron and Phosphorus Implanted Self-Aligned Bottom-Gate IGZO TFTs	
2:50 pm	Dong Hyuk Kim	AA05	(Student, Late News) Optimized Heterojunction Metal-Oxide Semiconductor Structures for High Perfo Indium-Tin-Oxide TFTs	rmance
3:10 pm			BREAK	
3:30 pm	Yuchen Zhou	AA06	(Student) Accurate Field-Effect Mobility Estimation with Gate Voltage-Dependent Mobility in Linear Re IGZO Thin-Film Transistors	gion for
3:50 pm	Hongseok Oh	AA07	IGZO Synaptic Thin-Film Transistors Using Embedded AlOx Charge-Trapping Layer	
4:10 pm	Reem Alshanbari	AA08	(Student) Tuning Threshold Voltage in Ultrathin Channel Flexible Amorphous InGaZnOx TFTs	
4:30 pm	Guoduan Liu	AA09	(Student) Improved Electrical Performance of InGaZnO <sub>4</sub> Thin-Film Transistors with UV Ozone Treatmen	nt
4:50 pm	William J. Scheideler	AA10	Continuous Liquid Metal Printing of High-Performance 2D Oxide Heterostructures	
BB: Gro	up III-Nitrides—P-Typ	e Dopii	ng and Characterization UC, Sant	a Barbara Harbo
1:30 pm	Shashwat Rathkanthiwar	BB01	Achieving Technologically Relevant P-Type Conductivity in Al-Rich (>70% Al) AlGaN Using Impurity Ba	and Conduction
1:50 pm	Cristyan E. Quiñones García	BB02	(Student) Modelling Self-Compensation in Heavily Mg-Doped GaN	
2:10 pm	Benjamin McEwen	BB03	MOCVD GaN Co-Doped with Mg and Be	
2:30 pm	Masahiro Kamiyama	BB04	(Student) Compensation Mechanism in Mg-Doped N-Polar GaN	
2:50 pm	Jia Wang	BB05	Observation of Spontaneous Intercalation of Interstitial Mg into GaN	
3:10 pm			BREAK	
3:30 pm	Emma Rocco	BB06	Investigation of Diffusion of Be and Mg Acceptor Dopant Implanted in GaN and the Impact of Annealin and Temperature	g Method
3:50 pm	Chandan Joishi	BB09	(Late News) Tunnel Junction Enabled AlGaN/GaN Heterojunction Bipolar Transistor with All n-Type Coi	ntacts
4:10 pm	Kenny Huynh	BB08	Dissolution of Mg Segregated Defects in Mg-Implanted GaN After Ultra-High-Pressure Annealing	
CC: Cha	racterization of Galliu	ım Oxio	de-Based Materials and Devices II	CC, MCC Theate
1:30 pm	Khandakar Aaditta Arnab	CC01	(Student) Temperature-Dependent Calculations of $\beta\text{-}Ga_2O_3$ Defect Concentrations for Equilibrium, Full Quenching and Generalized Quenching Scenarios	
1:50 pm	Kunyao Jiang	CC02	Phase Transformation of β-Ga <sub>2</sub> O <sub>3</sub> to Ga <sub>2</sub> O <sub>3</sub> -Based γ-Phase Spinels on (100) MgAl <sub>2</sub> O <sub>4</sub> Substrate	
2:10 pm	Jacqueline Cooke	CC03	Characterization Analysis of Extended Defects in β-Ga <sub>2</sub> O <sub>3</sub> and AGO	
2:30 pm	Ariful Islam	CC04	(Student) Temperature Dependence of Bandgap and Anisotropy in Urbach Tails in $\beta$ -Ga $_2$ O $_3$	
2:50 pm	Kenny Huynh	CC05	Crack Formation in Strained $\beta$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> Films Grown on (010) $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Substrates	
3:10 pm			BREAK	
DD: Gal	ium Oxide Materials F	Proces	sing M	CC, MCC Theate
3:30 pm	Zhenwei Wang	DD01	Improvement of Ga <sub>2</sub> O <sub>3</sub> Schottky Barrier Diode Characteristics by Nitrogen Radical Treatment	
3:50 pm	Saurav Roy	#DD02	(Student) Enhancing the Dielectric Performance of ${\rm Al_2O_3}$ on ${\rm \beta\text{-}Ga_2O_3}$ Using Temperature Modulated In Situ Dielectric Deposition	
4:10 pm	Cameron Anthony Gorsak	DD03	(Student) SIMS Study of the Accumulation of Si on the Surface of Gallium Oxide and Its Mitigation	
4:30 pm	Katie Gann	DD04	(Student) Optimizing Si Implantation and Annealing in $\beta\text{-}\text{Ga}_2\text{O}_3$	
4:50 pm	Alan G. Jacobs	DD05	Silicon Ion Implant Activation in $\beta$ -Al $_{0.4}$ Ga $_{1.6}$ O $_3$	

# Student Finalist for Oral Presentation

## FRIDAY AM

EE: Dian	nond and Related Ma	terials	UC, Corwin East
8:20 am	Dmitry Shinyavskiy	EE01	(Student) Synthesis of Free-Standing Polycrystalline Diamond Nanomembrane
8:40 am	Makoto Kasu	EE02	Characterization of Inch-Sized Diamond Wafer Grown on Misoriented Sapphire
9:00 am	Kaicheng Pan	EE03	(Student) Chemical Mechanical Polishing of Polycrystalline Diamond Films for Integration as High Thermal Conductivity Layers
9:20 am	Michael Spencer	EE04	Electronic and Optical Characterization of Bulk and Epitaxial Single Crystals of Cubic Boron Nitride (cBN)
9:40 am	Lillian Barrett Hughes	EE05	(Student) Two-Dimensional Spin Systems in PECVD-Grown Diamond with Tunable Density and Long Coherence for Enhanced Quantum Sensing and Simulation
10:00 am			BREAK
FF: Grou	p III-Nitrides—Thern	nal Trans	sport UC, Corwin East
10:20 am	MVS Chandrashekhar	FF01	Thermal Considerations in Co-Designed III-Nitride Transistors
10:40 am	James Spencer Lundh	FF02	Thermal Mapping of AlGaN/GaN High Electron Mobility Transistors Using Mechanically Exfoliated MoS <sub>2</sub> Flakes
11:00 am	Khush Mahendrakumar Gohel	FF03	(Student) Understanding of Multi-Way Heat Extraction Using Peripheral Diamond in AlGaN/GaN HEMT by Electrothermal Simulations
11:20 am	Luke Yates	FF04	Visualizing and Quantifying Thermal Conductance and Strain at Compression Bonded GaN-Diamond Interfaces via Optical Methods
GG: Epit	axy of Structured and	d Quant	um Materials UC, Flying A Studios
8:20 am	Alec Mason Skipper	GG01	(Student) Dark Current Reduction by MBE Selective Area Growth in III-V Semiconductor PIN Photodetectors
8:40 am	Yiteng Wang	GG02	(Student) InP Lateral Epitaxial Overgrowth by Solid-Source Molecular Beam Epitaxy
9:00 am	Ashlee Garcia	#GG03	(Student) SiO <sub>2</sub> Surface Planarization for Molecular Beam Epitaxy Selective Area Regrowth of High Aspect Ratio Microstructures
9:20 am	Mikolaj Chlipala	GG04	(Student) Light-Emitter/Superconducting Stack Within the Nitride Family
9:40 am	J. Andrew McArthur	GG05	(Student) Manipulating the Opto-Electronic Properties of Al <sub>x</sub> In <sub>1-x</sub> As <sub>y</sub> Sb <sub>1-y</sub> Digital Alloys by Adjusting the Period Thickness
10:00 am			BREAK
10:20 am	Brendan Jordan	GG06	(Student) Growth and Characterization of Multigrain SmB <sub>6</sub> Thin Films by Chemical Vapor Deposition
10:40 am	Yuxing Ren	GG07	(Student) Quasi van der Waals Epitaxy of Magnetic Topological Insulator on a GaAs (111) Substrate
11:00 am	Tri Nguyen	GG08	(Student) Electrical and Optical Properties of Sputtered SnTe
11:20 am	Rohit Yadav	GG09	(Student) Self-Limiting Formation of Bismuth-Induced Nanostructures on the InSb(111) Surface
11:40 am	Binghao Guo	GG10	(Student) Magnetotransport Studies of Two-Dimensional Cd <sub>3</sub> As, Heterostructures
HH: Mat	erials Processing and	d Integra	ation UC, State Street
8:20 am	Archit Shah	HH01	(Student) Fabrication of SU-8 Microstructures on Bulk Molybdenum Substrates for Cryogenic Applications
8:40 am	Florence A. Nugera	HH02	Growth of Patterned Diamond Using High Seeding Density and Hot-Filament Chemical Vapor Deposition (HFCVD)
9:00 am	Christopher Bishop	HH03	Experimental Characterization and Modification of Silicon Nitride Crystallization Reaction Kinetics for Microelectronics Applications
9:20 am	Eric Blanton	HH04	Investigation of Bonded GaN-Si p-n Junction Interface Properties
9:40 am	Lezli Matto	HH05	(Student) Thin-Film Layer Transfer of 128° Y-Cut LiNbO <sub>3</sub> on (0001) Al <sub>2</sub> O <sub>3</sub> Through Ion Implantation and Exfoliation
10:00 am			BREAK
10:20 am	Lukas Leonard Janavicius	HH06	(Student) Realization of Vapor-Phase MacEtch: Mechanism, Programmability and Scalability
10:40 am	Abhilasha Kamboj	HH07	(Late News) Substrate-Removed GaAs Photovoltaic Cells for Microscale Energy Harvesting
11:00 am	William J. Scheideler	HH08	(Late News) Anionic Engineering and 3D Integration of 2D Ti <sub>3</sub> C <sub>2</sub> T <sub>x</sub> MXene for Electrocatalysis and Energy Storage
11:20 am	B. Garfield	HH09	(Student, Late News) Development of Sustainable Non-Toxic TiO <sub>2</sub> /Sb <sub>2</sub> Se <sub>3</sub> Solar Cells for Renewable Energy Applications
11:40 am	Jared Mitchell	HH10	(Student, Late News) Probing Nonstoichiometry and Local Atomic Environments in GaAs, "N,Bi, Alloys



### **FRIDAY AM**

II: Flexib	le, Printed and Weara	able Ele	ctronics and Sensors UC, Lobe
8:20 am	Jung-Bin Ahn	II01	3D Printable Polymer Matrix Synthesis with UV-curable Polyurethane for Wearable Electronics
8:40 am	Annatoma Arif	1102	(Student) Characterization and Fabrication of 3D Inkjet Printed Flexible Copper Electrodes
9:00 am	Jee Young Kwak	1103	(Student, Late News) Carbon Based Omnidirectional Wearable Strain Sensor Arrays with Optimized Multi-Output Neural Networks
9:20 am	Nam-In Kim	1104	Highly Sensitive and Selective Cortisol Detection from Sweat Using Piezoelectric Single-Crystalline Flexible GaN Thin-Film Se
9:40 am	Lauren Kelly	1105	(Student) Electrochemical Detection of the LuxR Protein Using the Metabolic Activity of <i>Shewanella oneidensis</i> MR-1 for the Development of a Modular Bioelectronic Interface
10:00 am			BREAK
10:20 am	Andrew Bourhis	1106	(Student) Optimizing Dual-Gate IGZO TFTs for Long-Term Flexible Neural Interfaces
10:40 am	Jing Gu	1107	(Student) Integration of ZnO Thin-Film Transistor Array with Surgical Forceps for Minimally Invasive Robotic Surgery
11:00 am			
11:20 am	Kaori Yamamoto	1109	(Late News) Integrated Graphene FET Array for High Sensitive Detection of New Corona Virus with Automated Solution Exchange System
JJ: Low-	Dimensional Structu	res – Qı	uantum Dots, Wires and Wells UC, Santa Barbara Harb
8:20 am	Frank Bertram	JJ01	Carrier Capture into Individual InP Quantum Dots Directly Imaged by Nanoscale Cathodoluminescence Microscopy
8:40 am	Ruiqi Hu	JJ02	(Student) Electronic and Structural Properties of Rare-Earth Mono-Pnictide (RE-V) Nanoparticles in III-V Matrices
9:00 am	Yuanchang Zhang	JJ03	MBE Growth for Wafer Scale Uniformity in Low Density InAs Quantum Dots
9:20 am	Chen Shang	JJ04	Quantum Dot Morphology and Defect Configuration Anisotropy for III-V Laser Material Grown on Patterned Si Photonic Wafers
9:40 am	Eamonn T. Hughes	JJ05	(Student) Gradual Degradation via Dislocation Microloop Formation in InAs Quantum Dot Lasers on Si and GaAs
10:00 am			BREAK
KK: Micr	ro-LEDs		UC, Santa Barbara Harb
10:20 am	Sheikh Ifatur Rahman	KK01	(Student) Impact of Barrier Thickness and Doping on the Carrier Transport in MQW P-Down Green LEDs
10:40 am	Xuefeng Li	KK02	(Student) Carrier Dynamics in Blue, Cyan, and Green Commercial InGaN/GaN LEDs Measured by Small-Signal Electroluminescence
11:00 am	Xuefeng Li	KK03	(Student) Trap-Assisted Auger Recombination in Commercial Green InGaN/GaN LEDs
11:20 am	Seonghoon Lee	KK04	The Role of Zn-Precursor in the Formation of Environment-Friendly Highly Luminescent Colloidal Quantum Dots and R/G/B QLEDs with Inverted Structure
11:40 am	Tanay Tak	KK05	(Student, Late News) Electron Emission Microscopy of an Electrically Driven III-Nitride-Based LED: Evidence of Lateral Electron Injection at V-Defect Sidewalls
LL: Diele	ectrics, Ferroelectrics	and M	ultifunctional Oxides MCC, MCC Theat
9:00 am	Rainer Timm	LL02	Semiconductor-Oxide Interfaces of InAs-Based Ferroelectric and RRAM Devices
9:20 am	Harish Kumarasubramanian	LL03	(Student) Pushing the Limits of Switching Voltage, Leakage in Ultrathin BaTiO <sub>3</sub> Thin Films
9:40 am	Michael Patrick McGarry	LL04	Frequency-Dependent Conductivity of Mo-SiN, Granular Metals
10:00 am			BREAK
10:20 am	Nicholas C. Strandwitz	LL05	Porous Dielectric Thin Films for Advanced Dielectrics Using Molecular and Atomic Layer Deposition
10:40 am	Subhajit Mohanty	LL08	(Student, Late News) Effect of HfO <sub>2</sub> Dielectric Thickness on the DC-RF Dispersion in N-Polar GaN HEMTs
11:00 am	Pius Suh	LL09	(Late News) Magnetic Tunnel Junction Molecular Spintronics Based Chemical Sensing Device

# Student Finalist for Oral Presentation